



Market News

Gate driver IC 1EDN from Infineon offers industry-leading low power consumption and high robustness

Munich, Germany – November 3, 2016 – Infineon Technologies AG (FSE: IFX / OTCQX: IFNNY) introduces the 1EDN EiceDRIVER™ family. This 1-channel low-side gate driver IC is a perfect fit to drive MOSFETs, IGBTs as well as GaN power devices. Its pin-out and packages are fully compatible to the industry standard which eases the drop-in replacement for existing designs. Applications which can leverage the outstanding performance of the driver IC include telecom and industrial SMPS, [DC-DC converters](#), PFC in [electrical vehicle charging stations](#) as well as industrial applications such as AC [power tools](#), [UPS](#), [air conditioning](#) and fans. The new family also supports wireless charging applications.

Lower internal power consumption

Compared to other 1-channel low-side gate driver ICs, the 1EDN EiceDRIVER family from Infineon leads the industry in low internal power consumption. The low-ohmic output stages translate into a higher efficiency of more than 30 percent. This allows for additional design flexibility and driving more power devices whilst staying within the thermal budget.

The outputs of the 1EDN family feature an industry-leading reverse current robustness of 5 A. This eliminates the need for protection diodes when driving MOSFETs with large parasitic source inductances typically found in TO-220 or TO-247 packages. With the new driver ICs customers can thus save on both, BoM and PCB area.

The 1EDN portfolio excels by its -10 V input robustness securing a crucial safety margin against ground-shifts when driving gate-transformers. This extra noise robustness protects against electrical overstress of the inputs or latch-up of the driver IC. Additionally, the 1EDN family includes variants with separate source and sink output terminals. This eases the turn-on and turn-off speed optimization, concurrently saving one external diode. The 1EDN EiceDRIVER™ family is in volume production

For the Trade Press: INFPM201611.009e

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and will be showcased at electronica 2016. More information is available at www.infineon.com/1edn.

Infineon at electronica 2016 (November 8–11, 2016, Munich, Germany)

The world is getting smarter and more connected by the day. At electronica 2016 Infineon presents exciting demos and product solutions that are making tomorrow's cars, factories and homes smart, secure and energy-efficient. New products and demos can be discovered at booth 506 in hall A5; in-depth knowledge is offered through expert talks at the Infineon IoT Security Circle. Further information about this fair's highlights is available at www.infineon.com/electronica.

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